National Semiconductor

April 1993

74AC843 • 74ACT843
9-Bit Transparent Latch

General Description

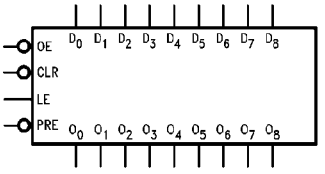
The 'AC/'ACT843 bus interface latch is designed to eliminate the extra packages required to buffer existing latches and provide extra data width for wider address/data paths.

The 'AC/'ACT843 is functionally and pin compatible with AMD's Am29843.

Features

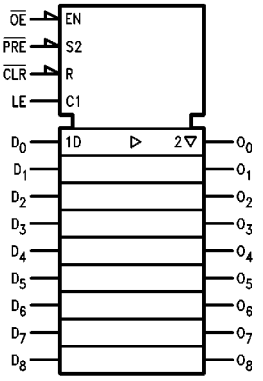
- 'ACT843 has TTL-compatible inputs
- TRI-STATE® outputs for bus interfacing

Logic Symbols



TL/F/9800–1

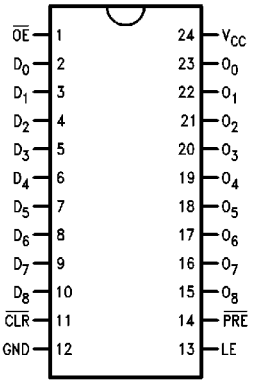
IEEE/IEC



TL/F/9800–3

Connection Diagram

Pin Assignment for DIP and SOIC



TL/F/9800–2

Pin Names	Description
D_0–D_8	Data Inputs
O_0–O_8	Data Outputs
$\overline{OE}$	Output Enable
LE	Latch Enable
$\overline{CLR}$	Clear
$\overline{PRE}$	Preset

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RRD-B30M75/Printed in U. S. A.

Functional Description

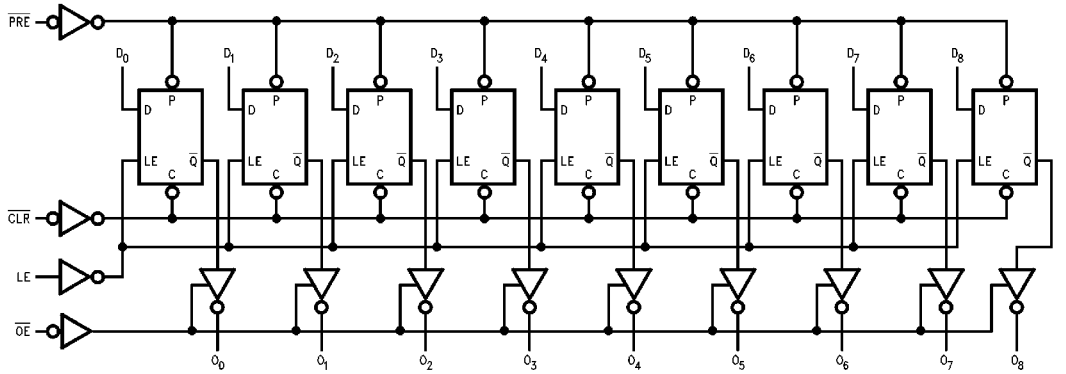
The 'AC/'ACT843 consists of nine D-type latches with TRI-STATE outputs. The flip-flops appear transparent to the data when Latch Enable (LE) is HIGH. This allows asynchronous operation, as the output transition follows the data in transition. On the LE HIGH-to-LOW transition, the data that meets the setup times is latched. Data appears on the bus when the Output Enable ($\overline{OE}$) is LOW. When $\overline{OE}$ is HIGH, the bus output is in the high impedance state. In addition to the LE and $\overline{OE}$ pins, the 'AC/'ACT843 has a Clear ($\overline{CLR}$) pin and a Preset ($\overline{PRE}$) pin. These pins are ideal for parity bus interfacing in high performance systems. When $\overline{CLR}$ is LOW, the outputs are LOW if $\overline{OE}$ is LOW. When $\overline{CLR}$ is HIGH, data can be entered into the latch. When $\overline{PRE}$ is LOW, the outputs are HIGH if $\overline{OE}$ is LOW. Preset overrides $\overline{CLR}$.

Function Tables

Inputs					Internal	Outputs	Function
$\overline{CLR}$	$\overline{PRE}$	$\overline{OE}$	LE	D	Q	O	
H	H	H	H	L	L	Z	High Z
H	H	H	H	H	H	Z	High Z
H	H	H	L	X	NC	Z	Latched
H	H	L	H	L	L	L	Transparent
H	H	L	H	H	H	H	Transparent
H	H	L	L	X	NC	NC	Latched
H	L	L	X	X	H	H	Preset
L	H	L	X	X	L	L	Clear
L	L	L	X	X	H	H	Preset
L	H	H	L	X	L	Z	Clear/High Z
H	L	H	L	X	H	Z	Preset/High Z

H = HIGH Voltage Level
L = LOW Voltage Level
X = Immaterial
Z = High Impedance
NC = No Change

Logic Diagram



TL/F/9800–5

Absolute Maximum Ratings (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Supply Voltage (V_{CC})	−0.5V to +7.0V
DC Input Diode Current (I_{IK})	
V_I = −0.5V	−20 mA
V_I = V_{CC} +0.5V	+20 mA
DC Input Voltage (V_I)	−0.5V to V_{CC} +0.5V
DC Output Diode Current (I_{OK})	
V_O = −0.5V	−20 mA
V_O = V_{CC} +0.5V	+20 mA
DC Output Voltage (V_O)	−0.5V to V_{CC} +0.5V
DC Output Source or Sink Current (I_O)	±50 mA
DC V_{CC} or Ground Current per Output Pin (I_{CC} or I_{GND})	±50 mA
Storage Temperature (T_{STG})	−65°C to +150°C
Junction Temperature (T_J)	
PDIP	140°C

Note 1: Absolute maximum ratings are those values beyond which damage to the device may occur. The databook specifications should be met, without exception, to ensure that the system design is reliable over its power supply, temperature, and output/input loading variables. National does not recommend operation of FACT™ circuits outside databook specifications.

Recommended Operating Conditions

Supply Voltage (V_{CC})	
'AC	2.0V to 6.0V
'ACT	4.5V to 5.5V
Input Voltage (V_I)	0V to V_{CC}
Output Voltage (V_O)	0V to V_{CC}
Operating Temperature (T_A)	
74AC/ACT	−40°C to +85°C
Minimum Input Edge Rate (ΔV/Δt)	
'AC Devices	
V_{IN} from 30% to 70% of V_{CC}	
V_{CC} @ 3.3V, 4.5V, 5.5V	125 mV/ns
Minimum Input Edge Rate (ΔV/Δt)	
'ACT Devices	
V_{IN} from 0.8V to 2.0V	
V_{CC} @ 4.5V, 5.5V	125 mV/ns

DC Electrical Characteristics for 'AC Family Devices

Symbol	Parameter	V_{CC} (V)	74AC T_A = +25°C	74AC T_A = −40°C to +85°C		Units	Conditions
			Typ	Guaranteed Limits			
V_{IH}	Minimum High Level Input Voltage	3.0	1.5	2.1	2.1	V	V_{OUT} = 0.1V or V_{CC} − 0.1V
		4.5	2.25	3.15	3.15		
		5.5	2.75	3.85	3.85		
V_{IL}	Maximum Low Level Input Voltage	3.0	1.5	0.9	0.9	V	V_{OUT} = 0.1V or V_{CC} − 0.1V
		4.5	2.25	1.35	1.35		
		5.5	2.75	1.65	1.65		
V_{OH}	Minimum High Level Output Voltage	3.0	2.99	2.9	2.9	V	I_{OUT} = −50 μA
		4.5	4.49	4.4	4.4		
		5.5	5.49	5.4	5.4		
		3.0		2.56	2.46	V	*V_{IN} = V_{IL} or V_{IH} I_{OH} −12 mA
		4.5		3.86	3.76		I_{OH} −24 mA
		5.5		4.86	4.76		I_{OH} −24 mA
V_{OL}	Maximum Low Level Output Voltage	3.0	0.002	0.1	0.1	V	I_{OUT} = 50 μA
		4.5	0.001	0.1	0.1		
		5.5	0.001	0.1	0.1		
		3.0		0.36	0.44	V	*V_{IN} = V_{IL} or V_{IH} I_{OL} 12 mA
		4.5		0.36	0.44		I_{OL} 24 mA
		5.5		0.36	0.44		I_{OL} 24 mA
I_{IN}	Maximum Input Leakage Current	5.5		±0.1	±1.0	μA	V_I = V_{CC}, GND

*All outputs loaded; thresholds on input associated with output under test.

DC Electrical Characteristics for 'AC Family Devices (Continued)

Symbol	Parameter	V_{CC} (V)	74AC $T_A = +25°C$		74AC $T_A = -40°C$ to $+85°C$	Units	Conditions
			Typ	Guaranteed Limits			
I_{OZ}	Maximum TRI-STATE Leakage Current	5.5		±0.5	±5.0	μA	V_I (OE) = V_{IL}, V_{IH} V_I = V_{CC}, GND V_O = V_{CC}, GND
I_{OLD}	†Minimum Dynamic Output Current	5.5			75	mA	V_{OLD} = 1.65V Max
I_{OHD}		5.5			−75	mA	V_{OHD} = 3.85V Min
I_{CC}	Maximum Quiescent Supply Current	5.5		8.0	80.0	μA	V_{IN} = V_{CC} or GND

†Maximum test duration 2.0 ms, one output loaded at a time.

Note: I_{IN} and I_{CC} @ 3.0V are guaranteed to be less than or equal to the respective limit @ 5.5V V_{CC}.

DC Electrical Characteristics for 'ACT Family Devices

Symbol	Parameter	V_{CC} (V)	74ACT $T_A = +25°C$		74ACT $T_A = -40°C$ to $+85°C$	Units	Conditions
			Typ	Guaranteed Limits			
V_{IH}	Minimum High Level Input Voltage	4.5 5.5	1.5 1.5	2.0 2.0	2.0 2.0	V	V_{OUT} = 0.1V or V_{CC} − 0.1V
V_{IL}	Maximum Low Level Input Voltage	4.5 5.5	1.5 1.5	0.8 0.8	0.8 0.8	V	V_{OUT} = 0.1V or V_{CC} − 0.1V
V_{OH}	Minimum High Level Output Voltage	4.5 5.5	4.49 5.49	4.4 5.4	4.4 5.4	V	I_{OUT} = −50 μA
		4.5 5.5		3.86 4.86	3.76 4.76	V	*V_{IN} = V_{IL} or V_{IH} I_{OH} −24 mA −24 mA
V_{OL}	Maximum Low Level Output Voltage	4.5 5.5	0.001 0.001	0.1 0.1	0.1 0.1	V	I_{OUT} = 50 μA
		4.5 5.5		0.36 0.36	0.44 0.44	V	*V_{IN} = V_{IL} or V_{IH} I_{OL} 24 mA 24 mA
I_{IN}	Maximum Input Leakage Current	5.5		±0.1	±1.0	μA	V_I = V_{CC}, GND
I_{OZ}	Maximum TRI-STATE Leakage Current	5.5		±0.5	±5.0	μA	V_I = V_{IL}, V_{IH} V_O = V_{CC}, GND
I_{CCT}	Maximum I_{CC}/Input	5.5	0.6		1.5	mA	V_I = V_{CC} − 2.1V
I_{OLD}	†Minimum Dynamic Output Current	5.5			75	mA	V_{OLD} = 1.65V Max
I_{OHD}		5.5			−75	mA	V_{OHD} = 3.85V Min
I_{CC}	Maximum Quiescent Supply Current	5.5		8.0	80.0	μA	V_{IN} = V_{CC} or GND

*All outputs loaded; thresholds on input associated with output under test.

†Maximum test duration 2.0 ms, one output loaded at a time.

AC Electrical Characteristics

Symbol	Parameter	V_{CC}* (V)	74AC $T_A = +25°C$, $C_L = 50$ pF			74AC $T_A = -40°C$ to $+85°C$, $C_L = 50$ pF		Units
			Min	Typ	Max	Min	Max	
t_{PLH}	Propagation Delay D_n to O_n	3.3	3.5	6.5	12.0	2.5	13.0	ns
		5.0	2.0	4.5	8.5	1.5	9.0	
t_{PHL}	Propagation Delay D_n to O_n	3.3	4.0	7.0	12.0	3.0	13.0	ns
		5.0	2.5	5.0	8.5	1.5	9.0	
t_{PLH}	Propagation Delay LE to O_n	3.3	3.5	6.5	12.0	13.0	2.5	ns
		5.0	2.0	4.5	8.5	1.5	9.0	
t_{PHL}	Propagation Delay LE to O_n	3.3	4.0	7.0	12.0	3.0	13.0	ns
		5.0	2.5	5.0	8.5	1.5	9.0	
t_{PLH}	Propagation Delay $\overline{PRE}$ to O_n	3.3	5.5	8.5	19.0	4.5	21.5	ns
		5.0	3.5	6.0	13.0	2.5	14.5	
t_{PHL}	Propagation Delay $\overline{CLR}$ to O_n	3.3	7.5	11.0	21.5	6.0	24.0	ns
		5.0	5.0	7.5	15.0	4.0	17.0	
t_{PZH}	Output Enable Time $\overline{OE}$ to O_n	3.3	3.5	6.0	11.0	3.0	12.0	ns
		5.0	2.0	4.5	8.0	1.5	9.0	
t_{PZL}	Output Enable Time $\overline{OE}$ to O_n	3.3	4.0	6.5	11.0	2.5	12.0	ns
		5.0	2.0	5.0	8.0	1.5	9.0	
t_{PHZ}	Output Disable Time $\overline{OE}$ to O_n	3.3	4.0	6.5	10.5	3.5	11.0	ns
		5.0	3.0	5.0	8.0	2.5	8.5	
t_{PLZ}	Output Disable Time $\overline{OE}$ to O_n	3.3	3.0	6.0	10.5	2.5	11.0	ns
		5.0	2.0	4.5	8.0	1.5	8.5	
t_{PHL}	Propagation Delay $\overline{PRE}$ to O_n	3.3	4.5	7.0	12.5	3.5	13.5	ns
		5.0	3.0	5.0	9.0	2.0	9.5	
t_{PLH}	Propagation Delay $\overline{CLR}$ to O_n	3.3	4.5	7.0	12.5	3.5	13.5	ns
		5.0	3.0	5.0	9.0	2.0	9.5	

*Voltage Range 3.3 is 3.3V ±0.3V

*Voltage Range 5.0 is 5.0V ±0.5V

AC Operating Requirements

Symbol	Parameter	V_{CC}* (V)	74AC $T_A = +25°C$, $C_L = 50$ pF		74AC $T_A = -40°C$ to $+85°C$, $C_L = 50$ pF	Units
			Typ	Guaranteed Minimum		
t_s	Setup Time, HIGH or LOW D_n to LE	3.3 5.0	0 −0.5	3.0 1.5	3.5 2.0	ns
t_h	Hold Time, HIGH or LOW D_n to LE	3.3 5.0	 −0.5	2.0 2.5	2.0 2.5	ns
t_w	LE Pulse Width, HIGH	3.3 5.0	1.5 1.5	3.0 3.0	3.0 3.0	ns
t_w	$\overline{PRE}$ Pulse Width, LOW	3.3 5.0	5.0 3.0	12.0 8.5	14.5 10.0	ns
t_w	$\overline{CLR}$ Pulse Width, LOW	3.3 5.0	5.5 4.0	14.0 10.0	16.5 12.0	ns
t_{rec}	$\overline{PRE}$ Recovery Time	3.3 5.0	1.0 0	3.0 1.5	3.0 1.5	ns
t_{rec}	$\overline{CLR}$ Recovery Time	3.3 5.0	0 −0.5	1.5 0.5	1.5 0.5	ns

*Voltage Range 3.3 is 3.3V ±0.3V

*Voltage Range 5.0 is 5.0V ±0.5V

AC Electrical Characteristics

Symbol	Parameter	V_{CC}* (V)	74ACT $T_A = +25°C$, $C_L = 50$ pF			74ACT $T_A = -40°C$ to $+85°C$, $C_L = 50$ pF		Units
			Min	Typ	Max	Min	Max	
t_{PLH}	Propagation Delay D_n to O_n	5.0	2.5	5.5	9.5	2.0	10.0	ns
t_{PHL}	Propagation Delay D_n to O_n	5.0	2.5	5.5	9.5	2.0	10.0	ns
t_{PLH}	Propagation Delay LE to O_n	5.0	2.5	5.5	9.0	2.0	10.0	ns
t_{PHL}	Propagation Delay LE to O_n	5.0	2.5	5.5	9.0	2.0	10.0	ns
t_{PLH}	Propagation Delay $\overline{PRE}$ to O_n	5.0	2.5	6.5	14.0	2.0	16.0	ns
t_{PHL}	Propagation Delay $\overline{CLR}$ to O_n	5.0	2.5	7.5	15.5	2.0	17.5	ns
t_{PZH}	Output Enable Time $\overline{OE}$ to O_n	5.0	2.5	5.5	9.5	2.0	10.5	ns
t_{PZL}	Output Enable Time $\overline{OE}$ to O_n	5.0	2.5	5.5	9.5	2.0	10.5	ns
t_{PHZ}	Output Disable Time $\overline{OE}$ to O_n	5.0	2.5	6.0	10.5	2.0	11.0	ns
t_{PLZ}	Output Disable Time $\overline{OE}$ to O_n	5.0	2.5	6.0	10.5	2.0	11.0	ns
t_{PHL}	Propagation Delay $\overline{PRE}$ to O_n	5.0	2.5	6.0	10.5	2.0	11.0	ns
t_{PLH}	Propagation Delay $\overline{CLR}$ to O_n	5.0	2.5	5.5	9.5	2.0	10.5	ns

*Voltage Range 5.0 is 5.0V ±0.5V

AC Operating Requirements

Symbol	Parameter	V_{CC}* (V)	74AC $T_A = +25°C$, $C_L = 50$ pF		74AC $T_A = -40°C$ to $+85°C$, $C_L = 50$ pF	Units
			Typ	Guaranteed Minimum		
t_s	Setup Time, HIGH or LOW D_n to LE	5.0	−0.5	0.5	1.0	ns
t_h	Hold Time, HIGH or LOW D_n to LE	5.0	0.5	2.0	2.0	ns
t_w	LE Pulse Width, HIGH	5.0	2.0	3.5	3.5	ns
t_w	$\overline{PRE}$ Pulse Width, LOW	5.0	5.0	8.5	10.0	ns
t_w	$\overline{CLR}$ Pulse Width, LOW	5.0	5.5	9.5	11.0	ns
t_{rec}	$\overline{PRE}$ Recovery Time	5.0	0.5	2.0	2.0	ns
t_{rec}	$\overline{CLR}$ Recovery Time	5.0	−0.5	1.0	1.0	ns

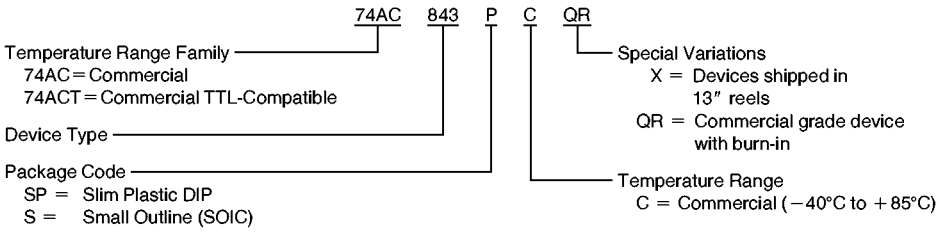
*Voltage Range 5.0 is 5.0V ±0.5V

Capacitance

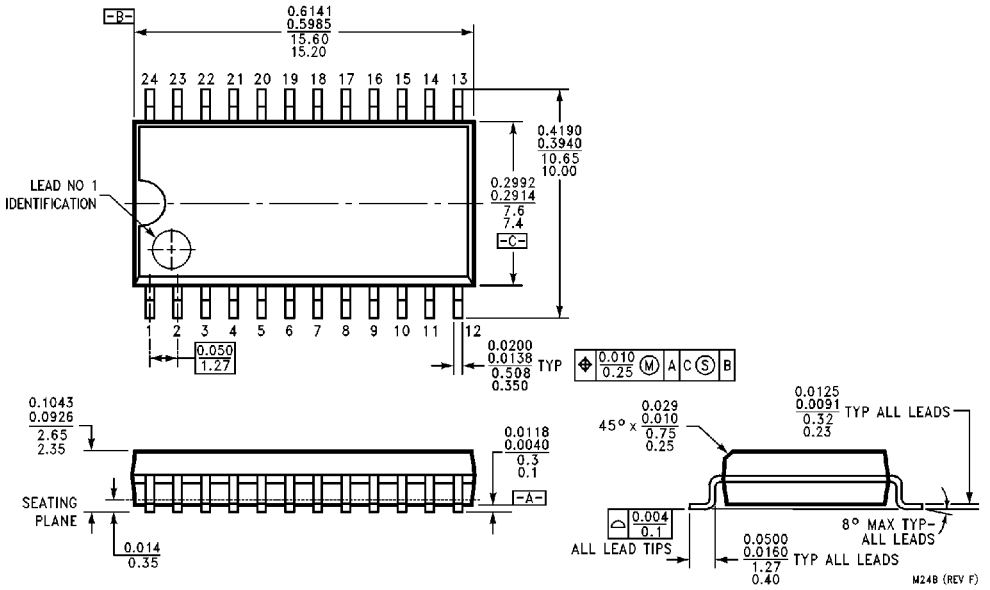
Symbol	Parameter	Typ	Units	Conditions
C_{IN}	Input Capacitance	4.5	pF	V_{CC} = OPEN
C_{PD}	Power Dissipation Capacitance	44	pF	V_{CC} = 5.0V

Ordering Information

The device number is used to form part of a simplified purchasing code where a package type and temperature range are defined as follows:



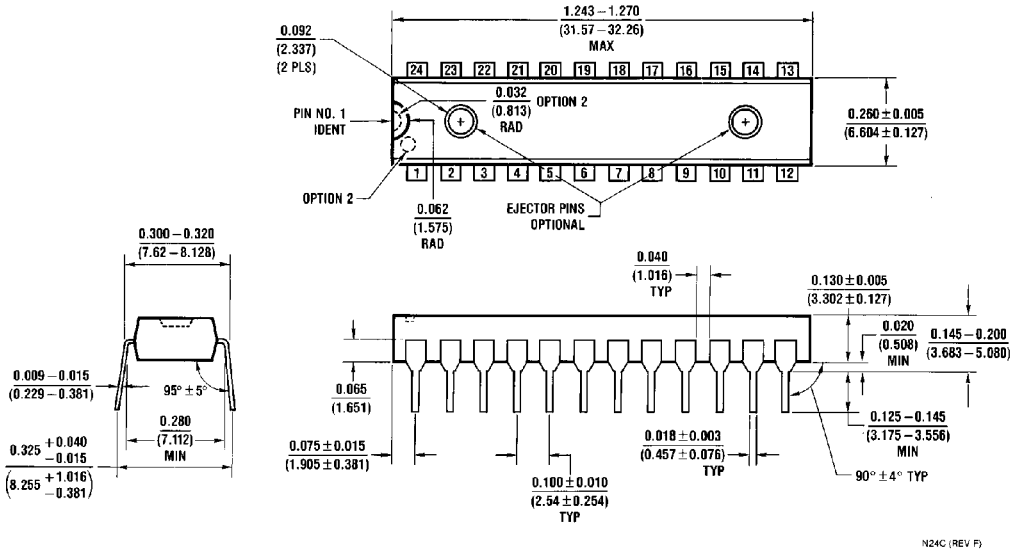
Physical Dimensions inches (millimeters)



24-Lead Small Outline Integrated Circuit (S)
NS Package Number M24B

Physical Dimensions inches (millimeters) (Continued)

Lit. # 114638



24-Lead Slim (0.300" Wide) Plastic Dual-In-Line Package (SP)
NS Package Number N24C

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